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With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



## Contact us

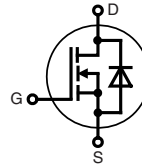
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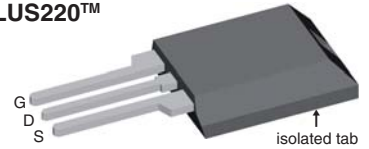
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# CoolMOS™ 1) Power MOSFET

Electrically isolated back surface  
 2500 V electrical isolation  
 N-Channel Enhancement Mode  
 Low  $R_{DS(on)}$ , high  $V_{DSS}$  MOSFET  
 Ultra low gate charge



$V_{DSS} = 600\text{ V}$   
 $I_{D25} = 15\text{ A}$   
 $R_{DS(on) \text{ max}} = 190\text{ m}\Omega$

**ISOPLUS220™**


E72873

MOSFET			
Symbol	Conditions	Maximum Ratings	
$V_{DSS}$	$T_{VJ} = 25^\circ\text{C}$	600	V
$V_{GS}$		$\pm 20$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	15	A
$I_{D90}$	$T_C = 90^\circ\text{C}$	10.5	A
$E_{AS}$	single pulse; $I_D = 10\text{ A}$ ; $T_C = 25^\circ\text{C}$	690	mJ
$E_{AR}$	repetitive; $I_D = 20\text{ A}$ ; $T_C = 25^\circ\text{C}$	1	mJ

**Features**

- Silicon chip on Direct-Copper-Bond substrate
  - high power dissipation
  - isolated mounting surface
  - 2500 V electrical isolation
  - low drain to tab capacitance ( $< 30\text{ pF}$ )
- CoolMOS™ 1) power MOSFET
  - 3rd generation
  - high blocking capability
  - lowest resistance
  - avalanche rated for unclamped inductive switching (UIS)
  - low thermal resistance due to reduced chip thickness
- Enhanced total power density

Symbol	Conditions	Characteristic Values			
		$(T_{VJ} = 25^\circ\text{C}, \text{ unless otherwise specified})$			
		min.	typ.	max.	
$R_{DS(on)}$	$V_{GS} = 10\text{ V}$ ; $I_D = 16\text{ A}$		160	190	m $\Omega$
$V_{GS(th)}$	$V_{DS} = V_{GS}$ ; $I_D = 1\text{ mA}$	2.1		3.9	V
$I_{DSS}$	$V_{DS} = 600\text{ V}$ ; $V_{GS} = 0\text{ V}$			25	$\mu\text{A}$
				250	$\mu\text{A}$
$I_{GSS}$	$V_{GS} = \pm 20\text{ V}$ ; $V_{DS} = 0\text{ V}$			100	nA
$C_{iss}$	} $V_{GS} = 0\text{ V}$ ; $V_{DS} = 25\text{ V}$ $f = 1\text{ MHz}$		2400		pF
$C_{oss}$				780	
$Q_g$	} $V_{GS} = 0\text{ to }10\text{ V}$ ; $V_{DS} = 350\text{ V}$ ; $I_D = 20\text{ A}$		87	114	nC
$Q_{gs}$			11		nC
$Q_{gd}$			33		nC
$t_{d(on)}$	} $V_{GS} = 13\text{ V}$ ; $V_{DS} = 380\text{ V}$ $I_D = 21\text{ A}$ ; $R_G = 3.3\ \Omega$ ; $T_{VJ} = 125^\circ\text{C}$		10		ns
$t_r$			5		ns
$t_{d(off)}$			67		ns
$t_f$			4.5		ns
$R_{thJC}$				1	K/W

**Applications**

- Switched mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)
- Power factor correction (PFC)
- Welding
- Inductive heating
- PDP and LCD adapter

**Advantages**

- Easy assembly: no screws or isolation foils required
- Space savings
- High power density
- High reliability

<sup>1)</sup> CoolMOS™ is a trademark of Infineon Technologies AG.

**Source-Drain Diode**

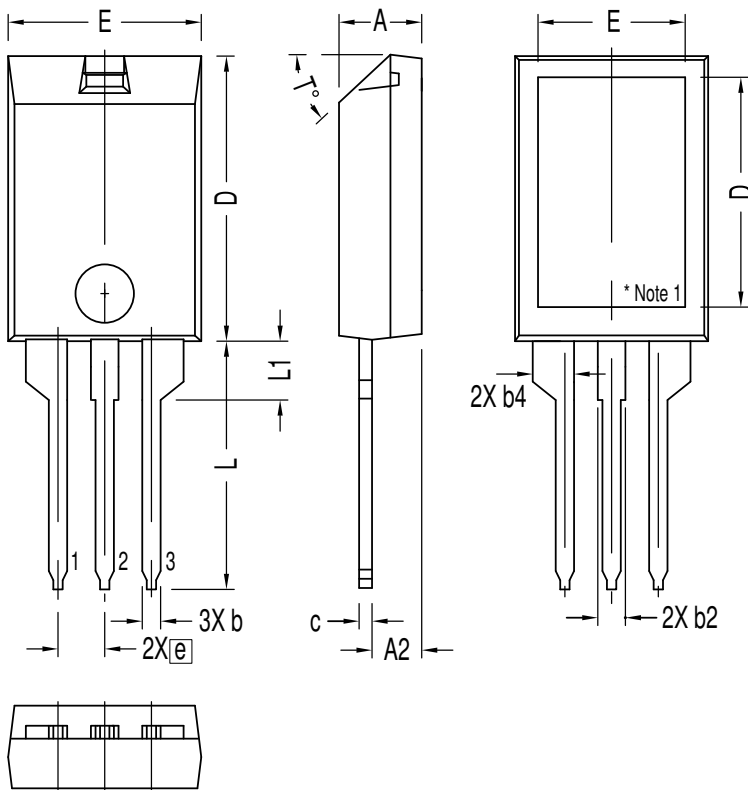
Symbol	Conditions	Characteristic Values			
		min.	typ.	max.	
( $T_{VJ} = 25^{\circ}\text{C}$ , unless otherwise specified)					
$I_S$	$V_{GS} = 0\text{ V}$			20	A
$V_{SD}$	$I_F = 16\text{ A}; V_{GS} = 0\text{ V}$		0.9	1.2	V
$t_{rr}$	$I_F = 20\text{ A}; -di_F/dt = 100\text{ A}/\mu\text{s}; V_R = 480\text{ V}$		500	800	ns
$Q_{RM}$			11		$\mu\text{C}$
$I_{RM}$			70		A

**Component**

Symbol	Conditions	Maximum Ratings	
$T_{VJ}$	operating	-55...+150	$^{\circ}\text{C}$
$T_{stg}$	storage	-55...+150	$^{\circ}\text{C}$
$V_{ISOL}$	RMS leads-to-tab, 50/60 Hz, $f = 1$ minute	2500	V~
$F_c$	mounting force	11-65 / 2.4-11	N/lb

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$R_{thCH}$	with heatsink compound		0.3	K/W
<b>Weight</b>			2.7	g

## ISOPLUS220™ Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.157	.197	4.00	5.00
A2	.098	.118	2.50	3.00
b	.035	.051	0.90	1.30
b2	.049	.065	1.25	1.65
b4	.093	.100	2.35	2.55
c	.028	.039	0.70	1.00
D	.591	.630	15.00	16.00
D1	.472	.512	12.00	13.00
E	.394	.433	10.00	11.00
E1	.295	.335	7.50	8.50
e	.100 BASIC		2.55	BASIC
L	.512	.571	13.00	14.50
L1	.118	.138	3.00	3.50
T°			42.5°	47.5°

NOTE:  
 1. Bottom heatsink is electrically isolated from Pin 1, 2, or 3.  
 2. This drawing will meet dimensional requirement of JEDEC SS Product Outline TO-273 except D and D1 dimension.

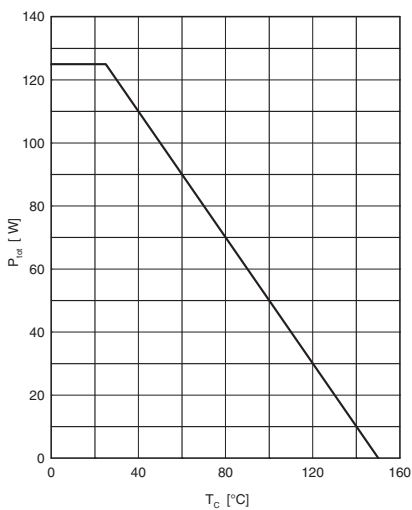


Fig. 1 Power dissipation

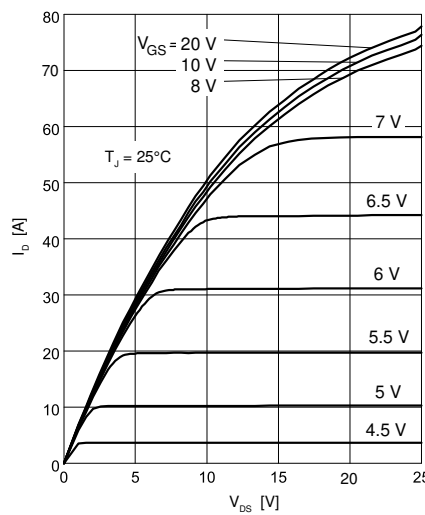


Fig. 2 Typ. output characteristics

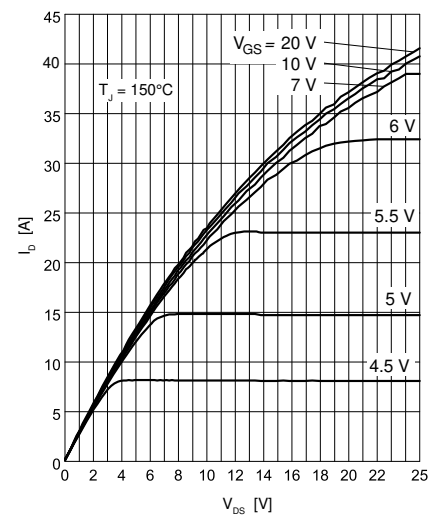


Fig. 3 Typ. output characteristics

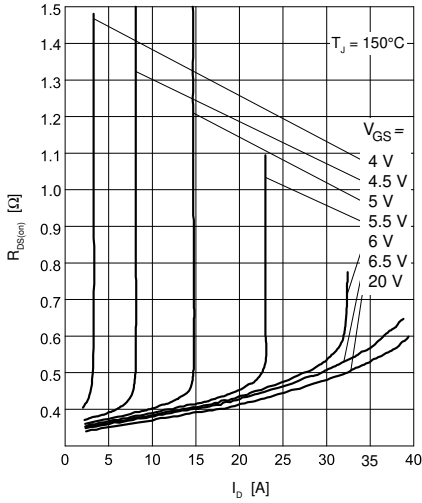


Fig. 4 Typ. drain-source on-state resistance

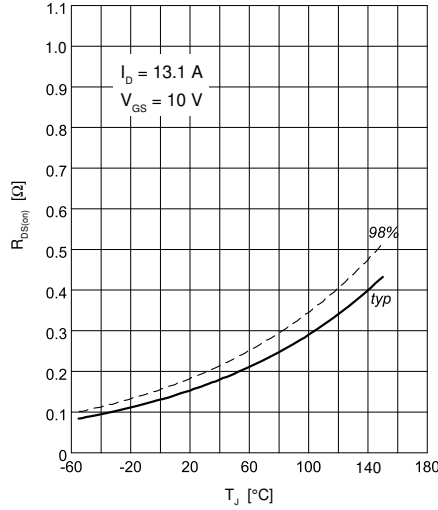


Fig. 5 Drain-source on-state resistance

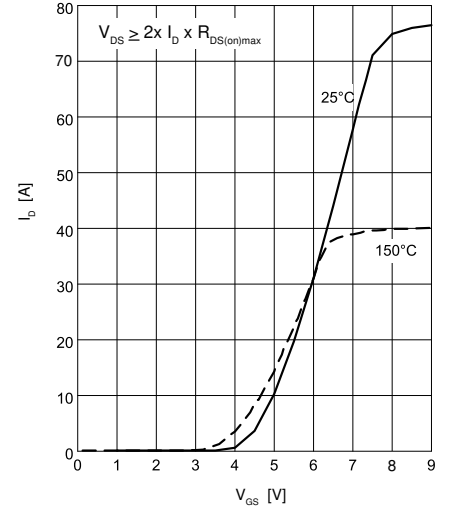


Fig. 6 Typ. transfer characteristics

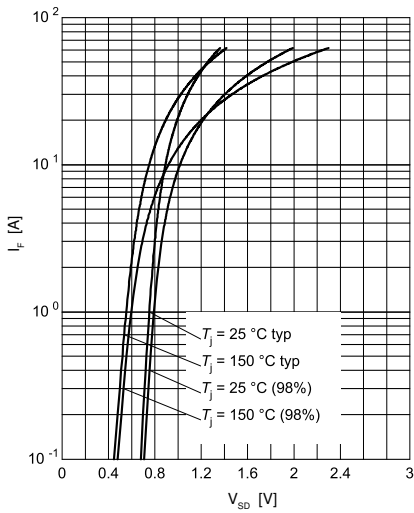


Fig. 7 Forward characteristic of reverse diode

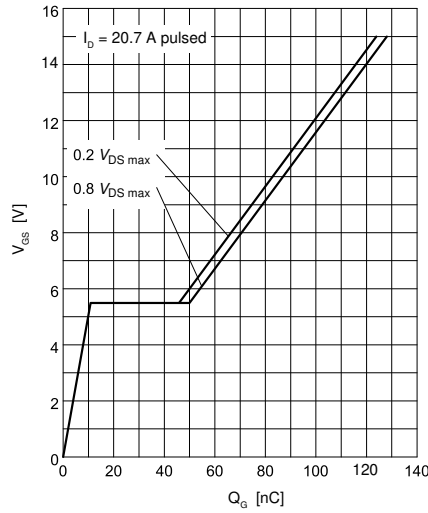


Fig. 8 Typ. gate charge

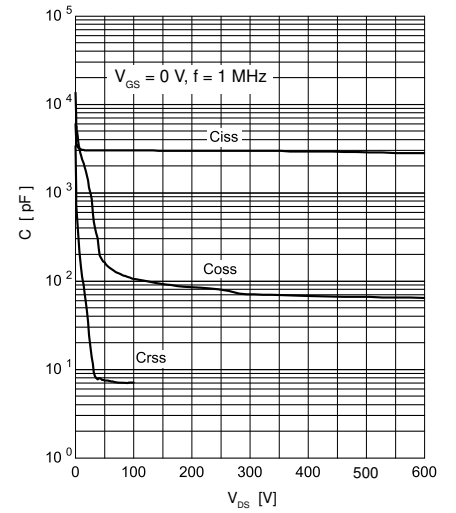


Fig. 9 Typ. capacitances

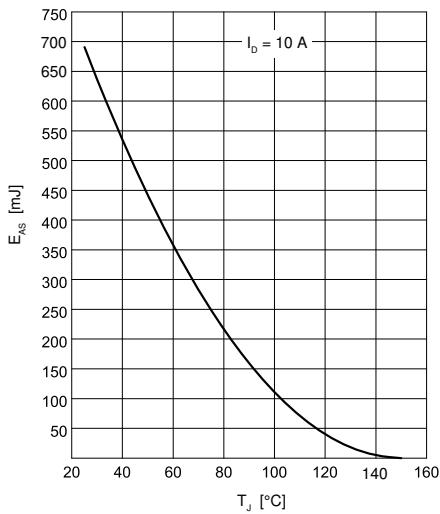


Fig. 10 Avalanche energy

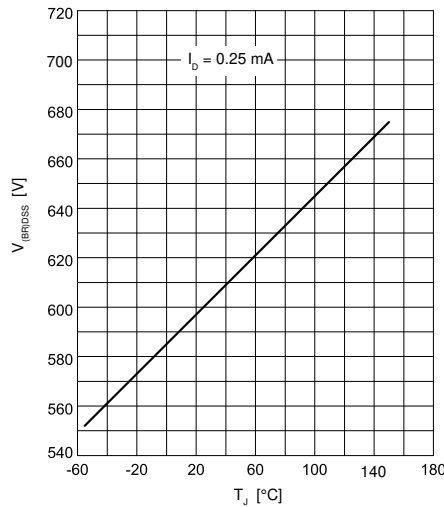


Fig. 11 Drain-source breakdown voltage